

# **SELFALIGNED PROCESS FOR A FLASH MEMORY**

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## **ABSTRACT OF THE DISCLOSURE**

10 A selfaligned process for a flash memory comprises  
applying a solution with a high etch selectivity to etch the  
sidewall of the tungsten silicide in the gate structure of the  
flash memory during a clean process before forming a spacer  
for the gate structure. This process prevents the gate  
structure from degradation caused by thermal stress.